

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	25			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		27		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1		2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 25 V, V _{GS} = 0 V			1	μA
		V _{DS} = 25 V, V _{GS} = 0 V, T _J = 55 °C			5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	50			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0052	0.0063	Ω
		V _{GS} = 4.5 V, I _D = 15 A		0.0064	0.008	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 20 A		85		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		1230		pF
Output Capacitance	C _{oss}			315		
Reverse Transfer Capacitance	C _{rss}			115		
Total Gate Charge	Q _g	V _{DS} = 12.5 V, V _{GS} = 10 V, I _D = 20 A		21.5	33	nC
		V _{DS} = 12.5 V, V _{GS} = 4.5 V, I _D = 20 A		9.3	14	
Gate-Source Charge	Q _{gs}			3.2		
Gate-Drain Charge	Q _{gd}			2.6		
Gate Resistance	R _g	f = 1 MHz		0.8	1.6	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 12.5 V, R _L = 12.5 Ω I _D ≅ 1.0 A, V _{GEN} = 4.5 V, R _g = 1 Ω		20	30	ns
Rise Time	t _r			28	42	
Turn-Off Delay Time	t _{d(off)}			30	45	
Fall Time	t _f			11	20	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 12.5 V, R _L = 12.5 Ω I _D ≅ 1.0 A, V _{GEN} = 10 V, R _g = 1 Ω		12	25	
Rise Time	t _r			15	25	
Turn-Off Delay Time	t _{d(off)}			30	45	
Fall Time	t _f			8	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			44.6	A
Pulse Diode Forward Current	I _{SM}				70	
Body Diode Voltage	V _{SD}	I _S = 4.0 A, V _{GS} = 0 V		0.75	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 4.0 A, dI/dt = 100 A/μs, T _J = 25 °C		26	50	ns
Body Diode Reverse Recovery Charge	Q _{rr}			24	50	nC
Reverse Recovery Fall Time	t _a			16.5		ns
Reverse Recovery Rise Time	t _b			9.5		

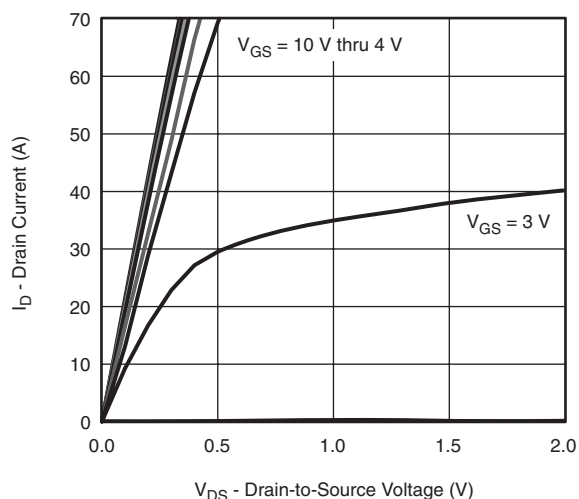
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

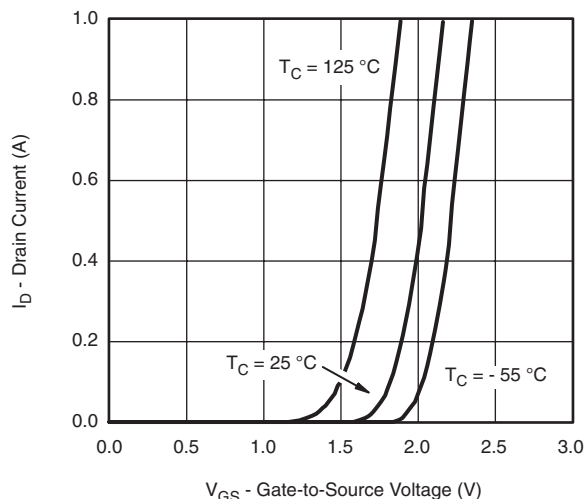
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

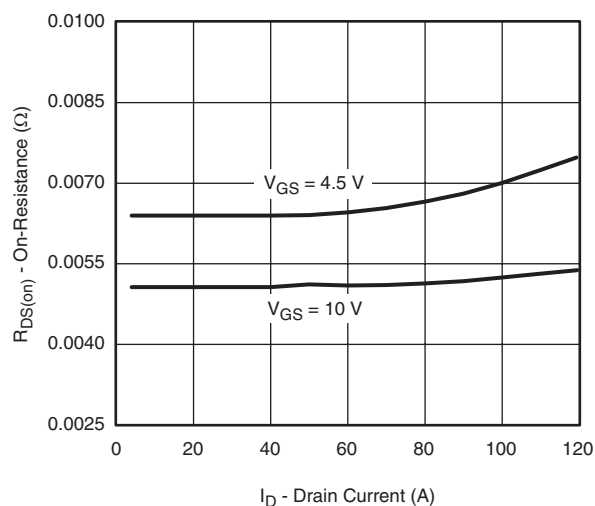
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



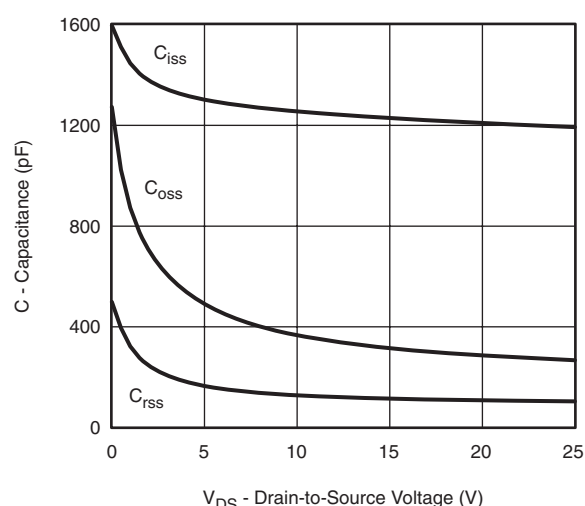
Output Characteristics



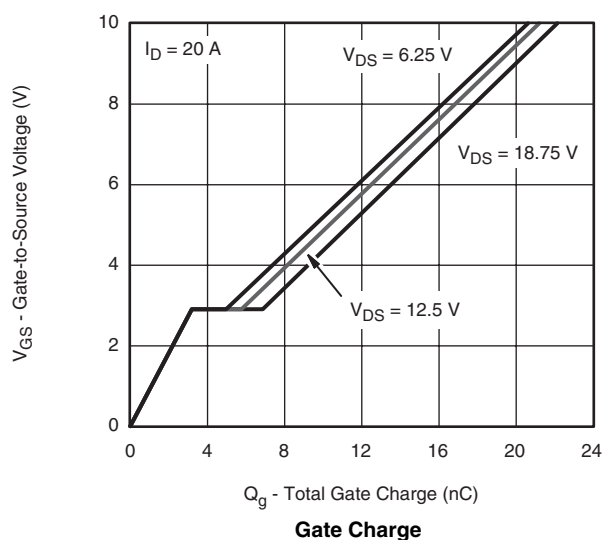
Transfer Characteristics



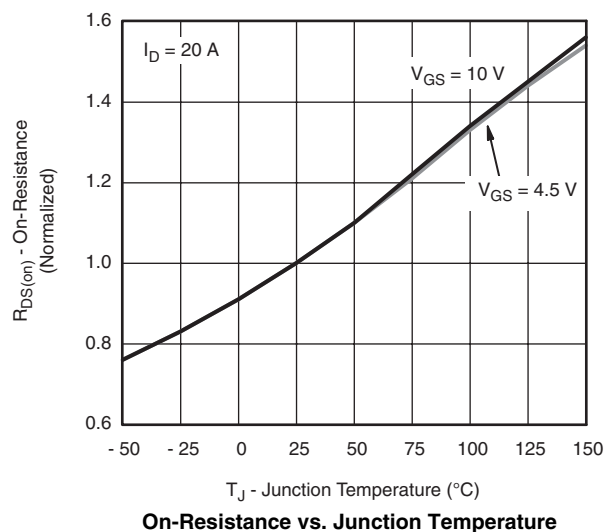
On-Resistance vs. Drain Current and Gate Voltage



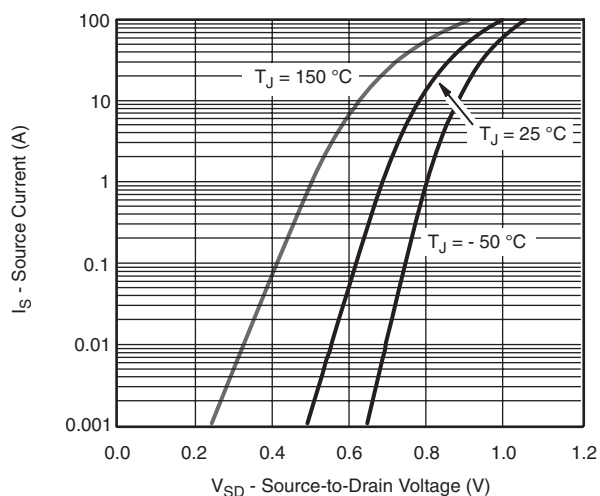
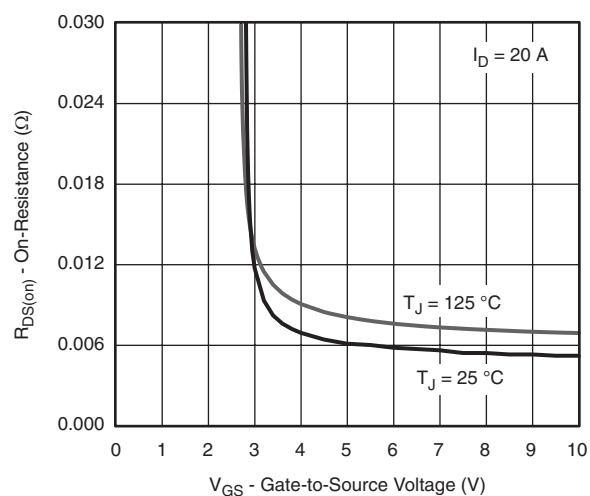
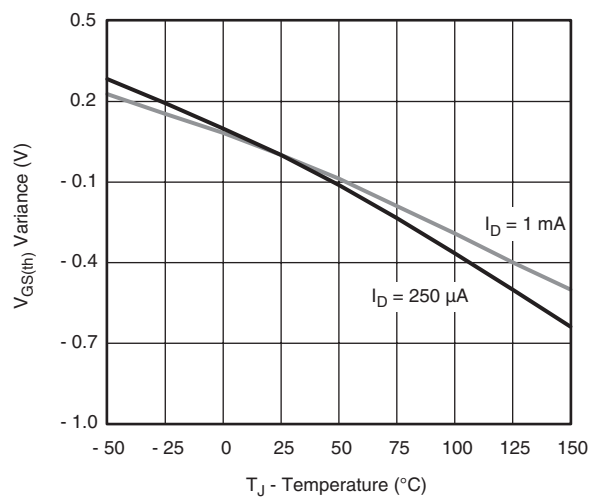
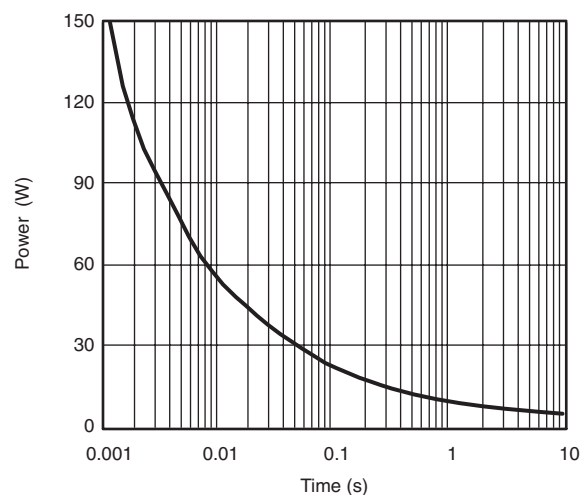
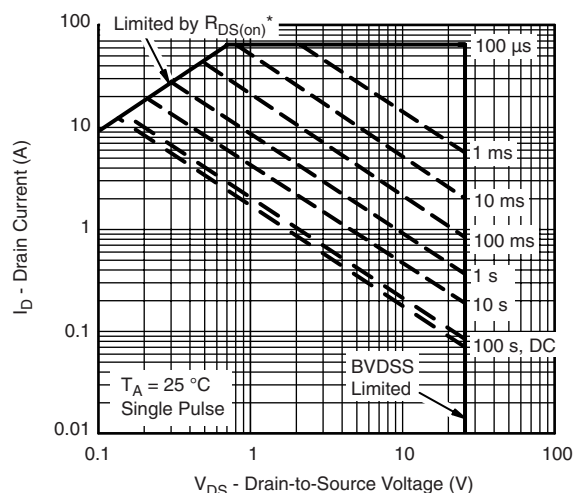
Capacitance



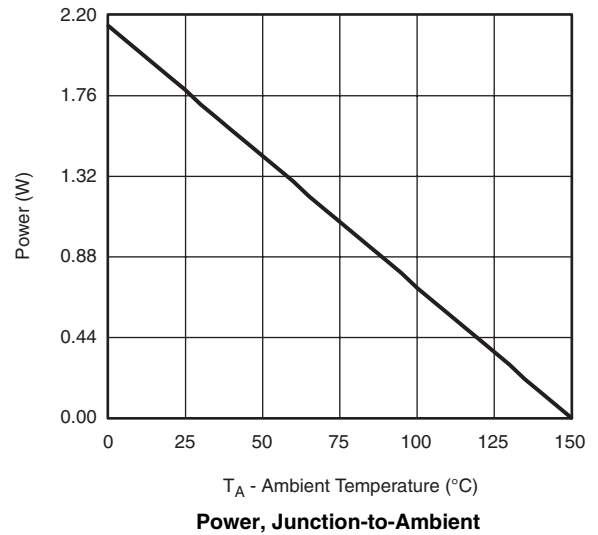
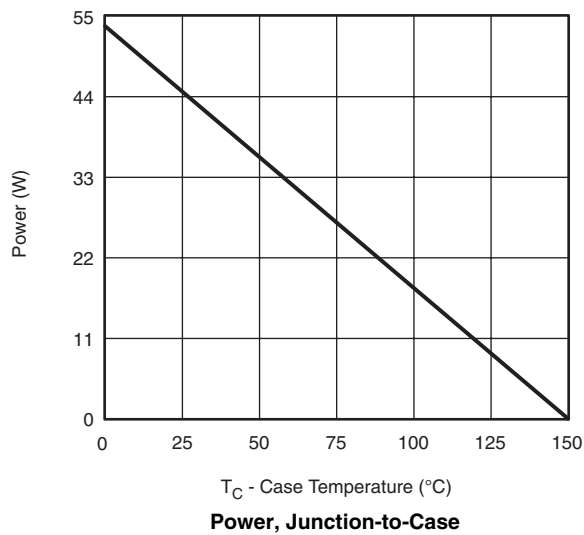
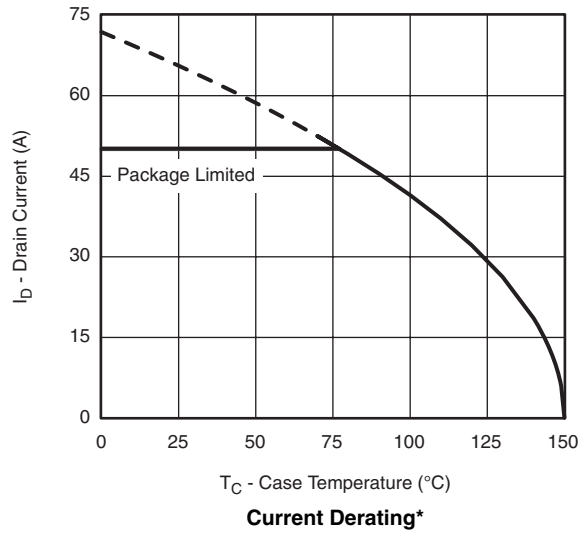
Gate Charge



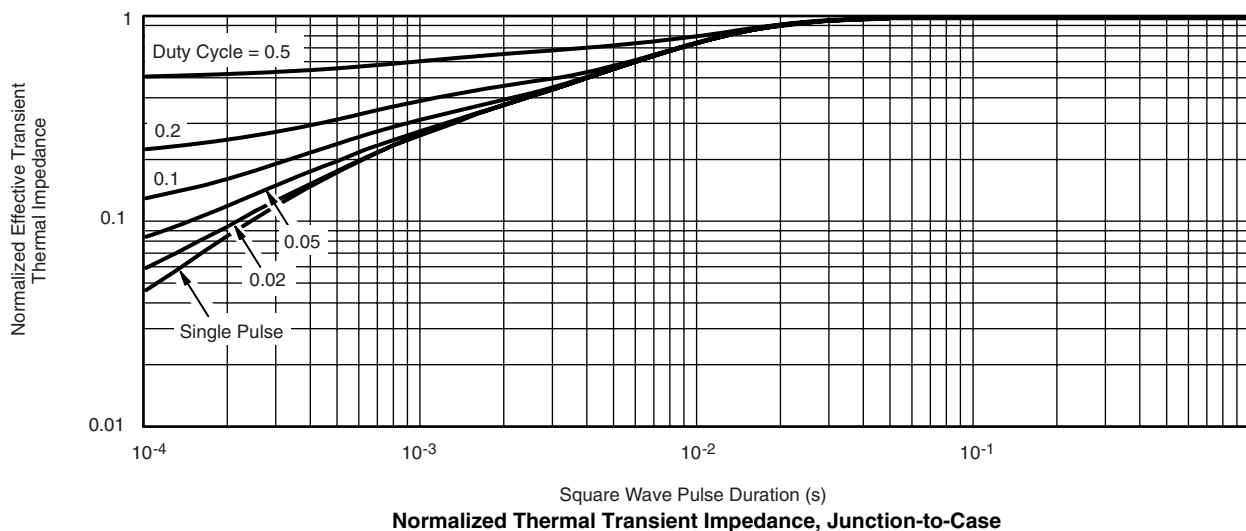
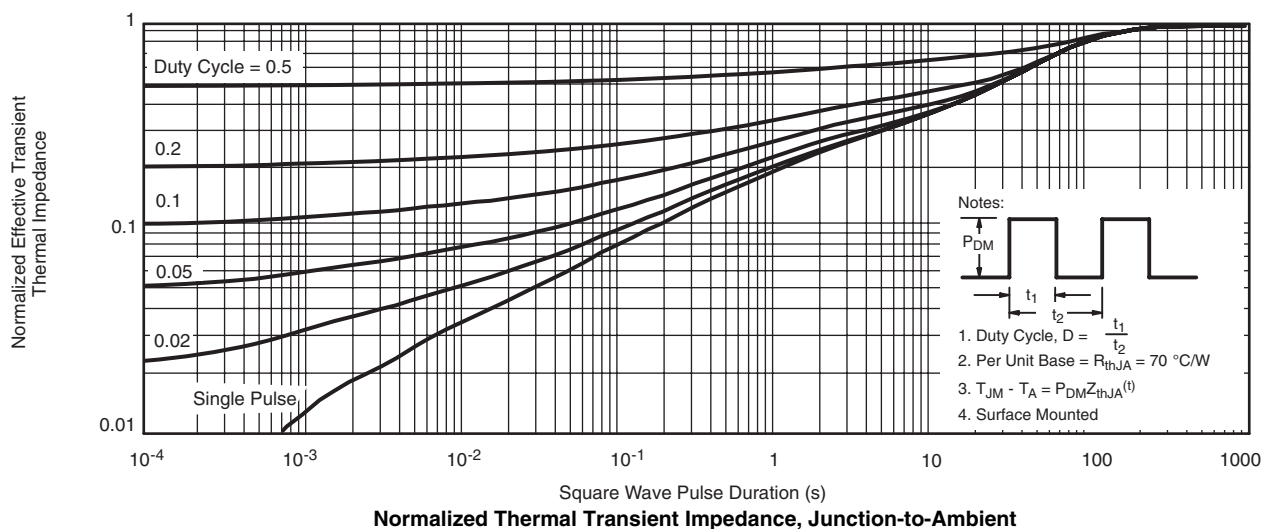
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power (Junction-to-Ambient)*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area, Junction-to-Ambient**

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* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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